

said wire connecting portion is composed of the same material as that for said electrical contact projection.

6. (Amended) A semiconductor device having a chip-on-chip structure in which a secondary chip is overlapped with and joined to a surface of a primary chip, wherein

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said primary chip comprises  
a surface protective film for covering internal wiring,  
an external connection pad formed by partially exposing the internal wiring from the surface protective film

a wire connecting portion which is formed using a metal material having oxidation resistance on the external connection pad and to which a wire for electrical connection to an external terminal is connected,

an internal connection pad which is formed by partially exposing said internal wiring from said surface protective film in a portion different from said external connection pad, and

an electrical contact projection which is formed in a raised state on the internal connection pad using a metal material having oxidation resistance for electrically connecting the primary chip and the secondary chip.

*Sub B2* > 7. (Amended) The semiconductor chip according to claim 6, wherein  
said wire connecting portion is composed of the same material as that for  
said electrical contact projection.

Please add new claim 10 as follows:

*Sub B3* > -- 10. (NEW) The semiconductor chip according to claim 6, further comprising a lead frame and a bonding wire, the bonding wire electrically interconnecting the lead frame and the wire connecting portion. --